Preliminary

TOSHIBA Photocoupler GaA{As IRED + Photo IC

TLP705

: 3mA (max)

: 10 to 20 V

: 10 kV/µs

: 5000 Vrms

: 200 ns (max)

: I_{FLH} = 8 mA (max)

:UL1577, File No.E67349

Plasma Display Panel. Industrial Inverter **IGBT/Power MOS FET Gate Drive**

TOSHIBA

The TOSHIBA TLP705 consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 6-lead SDIP package. TLP705 is 50% smaller than 8PIN DIP and has suited the safety standard reinforced insulation class. So mounting area in safety standard required equipment can be reduced. TLP705 is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP705 is capable of "direct" gate drive of lowr Power IGBTs.

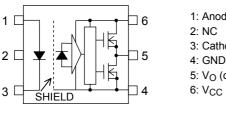
- Peak output current : ±0.45 A (max) •
- Operating frequency : 250kHz (max) •
- Guaranteed performance over temperature : -40 to 100°C ٠
- Supply current •
- Power supply voltage •
- Threshold input current
- Switching time (tpLH / tpHL) •
- Common mode transient immunity •
- Isolation voltage .
- **UL** Recognized
- Construction Mechanical Rating

	7.62 mm pich standard type	10.16 mm pich TLPXXXF type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.4 mm (Min)	0.4 mm (Min)

Truth Table

Input	LED	Tr1	Tr2	Output
Н	ON	ON	OFF	Н
L	OFF	OFF	ON	L

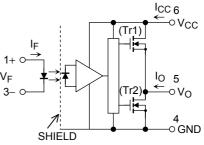
Pin Configuration (top view)



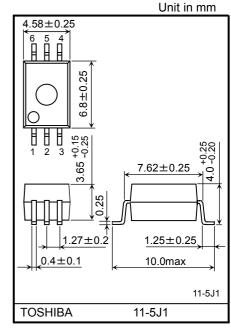


- 3: Cathode
- 4. GND
- 5: V_O (output)

Schematic



A 0.1 μF bypass capacitor must be connected between pin 6 and 4. (See Note 6)



Weight: 0.26 g (typ.)

Maximum Ratings (Ta = 25°C)

	Characteristics	Symbol	Rating	Unit	
	Forward current			20	mA
	Forward current derating (Ta ≥ 85°C)		ΔI _F /ΔTa	-0.54	mA/°C
LED	Peak transient forward current	(Note 1)	I _{FP}	1	А
	Reverse voltage		V _R	5	V
	Junction temperature		Tj	125	°C
	"H" peak output current	(Note 2)	I _{OPH}	-0.45	А
Ŀ	L" peak output current	(Note 2)	I _{OPL}	0.45	А
Detector	Output voltage		Vo	25	V
ă	Supply voltage		V _{CC}	25	V
	Junction temperature		Tj	125	°C
Oper	rating frequency	(Note 3)	f	250	kHz
Storage temperature range			T _{stg}	–55 to 125	°C
Operating temperature range			T _{opr}	-40 to 100	°C
Lead	I soldering temperature (10 s)	(Note 4)	T _{sol}	260	°C
Isola	tion voltage (AC, 1 minute, R.H. ≤ 60%)	(Note 5)	BVS	5000	Vrms

Note 1: Pulse width $P_W \le 1\mu s$, 300 pps

Note 2: Exponential waveform pulse width PW \leq 10 μ s , f \leq 15 kHz

Note 3: Exponential waveform IoPH ≤-0.25 A (≤80 ns) , IoPL ≤+0.25 A (≤80 ns) ,Ta =100 °C

Note 4: It is effective soldering area of Lead .

- Note 5: Device considerd a two terminal device: pins 1, 2 and 3 shorted together, and pins 4, 5 and 6 shorted together.
- Note 6: A ceramic capacitor(0.1 μF) should be connected from pin 6 to pin 4 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.

Recommended Operating Conditions

Characteristics		Symbol	Min	Тур.	Max	Unit
Input current, ON	(Note 7)	I _{F (ON)}	10	_	15	mA
Input voltage, OFF		V _{F (OFF)}	0	_	0.8	V
Supply voltage		V _{CC}	10	_	20	V
Peak output current		I _{OPH} / I _{OPL}	_	_	± 0.15	А
Operating temperature		T _{opr}	- 40	_	100	°C

Note 7: Input signal rise time (fall time) $< 0.5 \,\mu$ s.

Electrical Characteristics (Ta = -40 to 100°C, unless otherwise specified)

Characteristics		Symbol	Test Circu it	Test Condition		Min	Typ.*	Мах	Unit
Forward voltage		VF	_	I _F = 10 mA, Ta = 2	25°C	_	1.6	1.8	V
Temperature coefficient of forward voltage		∆V _F /∆Ta	_	I _F = 10 mA			-2.0		mV/°C
Input reverse current		I _R	—	V _R = 5 V, Ta = 25	°C	—	—	10	μA
Input capacitance		CT	_	V = 0 V, $f = 1 MH$	z,Ta = 25°C		45		pF
	"L" Lovel	I _{OPH1}	1	V _{CC} = 15 V	$V_{6-5} = 4 V$	-0.15	-0.35		A
Output current (Note 8)	"H" Level	I _{OPH2}		I _F = 10 mA	V ₆₋₅ = 10 V	-0.3	-0.6		
	"I" I	I _{OPL1}	2		$V_{5-4} = 2 V$	0.15	0.36		
	"L" Level	I _{OPL2}			V ₅₋₄ = 10 V	0.3	0.62		
Output voltage	"H" Level	V _{OH}	3)/a a _ 10)/	$I_{O} = -100 \text{ mA},$ $I_{F} = 10 \text{ mA}$	6.0	8.5		v
Output voltage	"L" Level	V _{OL}	4	V _{CC} = 10 V	$I_{O} = 100 \text{ mA},$ $V_{F} = 0.8 \text{ V}$	_	0.4	1.0	
Oursely summer t	"H" Level	Іссн	5	V _{CC} = 10 to 20 V	I _F = 10 mA		2.0	3.0	
Supply current	"L" Level	I _{CCL}	6	V _O open	$I_F = 0 \text{ mA}$	_	2.0	3.0	mA
Threshold input current	$L\toH$	I _{FLH}	—	V _{CC} = 15 V, V _O > 1 V		—	2.5	8	mA
Threshold input voltage	$H \to L$	V _{FHL}	—	V _{CC} = 15 V, V _O < 1 V		0.8	_	—	V
Supply voltage		V _{CC}	_	_		10	_	20	V

*: All typical values are at $Ta = 25^{\circ}C$

Note 8: Duration of I_O time \leq 50 µs

Note 9: This product is more sensitive than the conventional product to static electricity (ESD) because of a lowest power consumption design.

General precaution to static electricity (ESD) is necessary for handling this component.

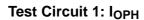
Isolation Characteristics (Ta = 25°C)

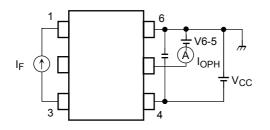
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0 V, f = 1MHz (Note 5)	_	1.0	_	pF
Isolation resistance	R _S	R.H. ≤ 60%,V _S = 500V (Note 5)	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage	BVS	AC, 1 minute	5000	_		Vrms
		AC, 1 second, in oil	_	10000		VIIIS
		DC,1 minute,in oil	_	10000	-	Vdc

Switching Characteristics (Ta = -40 to $100^{\circ}C$, unless otherwise specified)

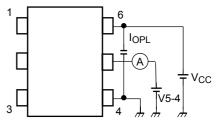
Characteristics		Symbol	Test Circuit	Test C	condition	Min	Typ.*	Max	Unit				
Propagation delay time	$L \to H$	t _{pLH}		Ta= 25 I _F = 0 10 mA	70	95	170						
i topagation delay time	$H \to L$	t _{pHL}			Ta= 25 I _F = 10→ 0 mA	70	105	170					
Descention delessions	$L\toH$	t _{pLH}	$V_{CC} = 20 V$ $R_g = 30 \Omega$ $C_g = 1 nF$	Ta= -40 to100 I _F = 0 10 mA	50		200						
Propagation delay time	$H \to L$	t _{pHL}		$R_g = 30 \Omega$ $C_a = 1 nF$	Ta= -40 to100 I _F = 10 0 mA	50		200					
Propagation delay difference between any two parts or channels		tpsk	- 7	f=250kHz Duty Cycle =50%	Ta= -40 to100 I _F = 10 mA	-90	_	90	ns				
Pulse Width Distortion		PWD (t _{pHL} -t _{pLH)}							Ta= -40 to100 I _F = 10 mA	-65	—	65	
Output rise time (10-90%)		tr			$I_F=0 \rightarrow 10 \text{ mA}$		_	_					
Output fall time (90-10%)		t _f			$I_F = 10 \rightarrow 0 \text{ mA}$		_						
Common mode transient i at hight level output	mmunity	CMH			V _{CM} = 1000Vp-p	$I_F = 10 \text{ mA}$ V _{O (min)} = 16 V	-10000	_	_	- V/μs			
Common mode transient immunity at low level output		CML	8	V _{CC} = 20 V Ta = 25°C	$I_F = 0 \text{ mA}$ $V_O \text{ (max)} = 1 \text{ V}$	10000		_	v/µs				

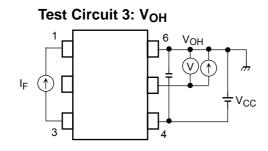
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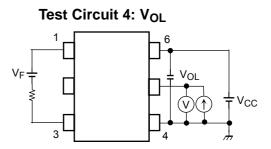


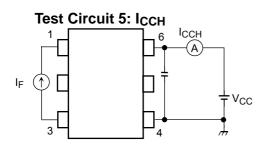


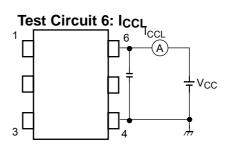




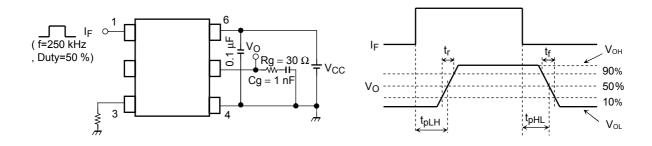




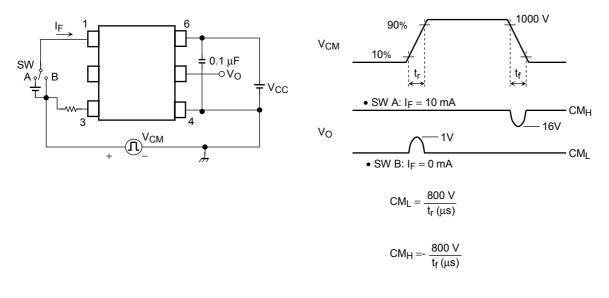




Test Circuit 7 : tpLH, tpHL, tr, tf, PWD



Test Circuit 8: CMH, CML



 CM_L (CM_H) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

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